November 4, 2004

PATENT APPLICATION DOCKET NO.: 0717.2033-002

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Jagdish Narayan

Application No.:

10/608,780

Group Art Unit:

2818

Filed:

June 27, 2003

Examiner:

Nhu, David

Confirmation No.:

8117

Title:

DOMAIN EPITAXY FOR THIN FILM GROWTH

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SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Comm P.O. B	stop Amendment hissioner for Patents fox 1450 hdria, VA 22313-1450) :	11/09/2004 NF 02 FC:1806	OCHA1	00000034 1060	08780 180.00 OP
Sir:						
This I	nformation Disclosure Statement is submitted: under 37 CFR 1.129(a), or (First/Second submission after Final Rejection)					
[]	under 37 CFR 1.97(b), or (Within any one of the following time periods: three months of filing no stage in an international application; or before the mailing date of a first CPA, or a Request for Continued Examination).					
[X]	under 37 CFR 1.97(c) together with either: [] a Statement under 37 CFR 1.97(e), as che [X] a \$180.00 fee under 37 CFR 1.17(p), or					
[]	(After the 37 CFR 1.97(b) time period, but before final action or notice under 37 CFR 1.97(d) together with: [] a Statement under 37 CFR 1.97(e), as characteristics.			eurs fīrs	:)	

(Filed after final action or notice of allowance, whichever occurs first, but on or before payment of the issue fee)

a \$180.00 fee under 37 CFR 1.17(p), or

[] under 37 CFR 1.97(i):

Applicant requests that the IDS and cited reference(s) be placed in the application filewrapper. (Filed after payment of issue fee)

Statement Under 37 CFR 1.97(e)

[]	any co	Each item of information contained in this Information Disclosure Statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement; or							
[]	No item of information contained in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the undersigned, after making reasonable inquiry, no item of information contains the information disclosure statement was known to any individual designated in 37 CFR 1.56(c) more than three months prior to the filing of this Information Disclosure Statement.								
<u>S</u> 1	tatem	ent Un	der 37 (CFR 1.704(d) (Patent Term Adjustment) Applies to original applications (other than design) filed on or after May 29, 2000						
[]	comm	unication ot receiv	information contained in the Information Disclosure Statement was cited in a son from a foreign patent office in a counterpart application and this communication yed by any individual designated in § 1.56(c) more than thirty days prior to the information Disclosure Statement.						
[]	X]	Enclos	sed here	with is form PTO-1449:						
		[X]		s of the cited references AC8-AK8, AA9-AK9, AA10-AG10, AP6-AQ6, AL7-AL8, AV6-AZ6 and AR7 are enclosed.						
			[]	Since this application was filed after June 30, 2003, copies of issued U.S. patents and published U.S. applications are not required and are not being provided.						
		[]	Applic	s of the cited references are enclosed except those entered in prior application, U.S. cation No. [], to which priority under 35 U.S.C. 120 is claimed. [The earlier ation contains copies of the cited references.]						
		[]	The list	sted references were cited in the enclosed International Search Report in a erpart foreign application.						
		[X]	The "c	concise explanation" requirement (non-English references) for reference AQ6, AP7 Q7 under 37 CFR 1.98(a)(3) is satisfied by:						
			[]	the explanation provided on the attached sheet.						
			[]	the explanation provided in the Specification.						
			[]	submission of the enclosed International Search Report.						
			[]	submission of the enclosed English-language version of a foreign Search Report and/or foreign Office Action.						
			[X]	the enclosed English language abstract.						

[]	Applie	cant requests that the following r	non-published pending applic	cations be considered:
Examiner's Initials		•		
		U.S. Patent Application No. [], by [inventor(s)], filed [], Docket No.: []
		U.S. Patent Application No. [], by [inventor(s)], filed [], Docket No.: []
		U.S. Patent Application No. [], by [inventor(s)], filed [], Docket No.: []
		Examiner	Date	_
	[]	A copy of each above-cited app	plication, including the curre	ent claims, is enclosed.
	[]	A copy of each above-cited appropriate those entered in prior application 35 U.S.C. 120 is claimed.	plication, including the curre on, U.S. Application No. [ent claims, is enclosed, excep], to which priority under
The E	xamine nces we	r is requested to return a copy of ere considered with the next office	the above list of pending ap ce communication.	plications indicating which
It is re	questec	d that the information disclosed l	nerein be made of record in t	his application.
Metho	od of pa	yment:		
[X]	A che accom	ck for the fee noted above is encupanying Reply. A copy of this	closed, or the fee has been inc Statement is enclosed.	cluded in the check with the
[]	Please enclos	e charge Deposit Account 08-038 sed.	80 in the amount of \$[]. A copy of this Statement is
[X]	Please	e charge any deficiency in fees a	nd credit any overpayment to	Deposit Account 08-0380.
		1	Respectfully submitted,	
			By N. Scott Rierce Registration No.: 34,900 Telephone: (978) 341-0036 Facsimile: (978) 341-0136	<u> </u>

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SUPPLEMENTAL INFORMATION DISCOSURE
CITATION
IN AN APPLICATION

November 4, 2004

(Use several sheets if necessary)

ATTORNEY DOCKET NO. 0717.2033-002

 $\begin{array}{c} \text{APPLICATION NO.} \\ 10/608,\!780 \end{array}$

FIRST NAMED INVENTOR Jagdish Narayan

filing date
June 27, 2003

EXAMINER CONFII Nhu, David 8117

CONFIRMATION NO. GF

GROUP 2818

U.S. PATENT DOCUMENTS						
EXAM- INER INI- TIAL	REF. NO.	DOCUMENT NUMBER Number-Kind Code (if known)	ISSUE DATE / PUBLICATION DATE MM-DD-YYYY	NAME OF PATENTEE OR APPLICANT OF CITED DOCUMENT		
	AC8	6,495,862 B1	12-17-2002	Okazaki et al.		
	AD8	US 2001/0032976 A1	10-25-2001	Ishikawa <i>et al</i> .		
	AE8	US 2002/0001864 A1	01-03-2002	Ishikawa <i>et al</i> .		
	AF8	US 2002/0182765 A1	12-05-2002	Tran et al.		
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EXAMINER	DATE CONSIDERED

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PTO-1449 REPRODUCED A CHERN EMENITAL INCORMATION DISCLOSURE			APPLICATION NO. 10/608,780	
SUPPLEMENTAL INFORMATION DISCLOSURE CITATION IN AN APPLICATION	FIRST NAMED INVENTOR Jagdish Narayan		FILING DATE June 27, 2003	
November 4, 2004 (Use several sheets if necessary)	EXAMINER Nhu, David	CONF 8117	IRMATION NO.	GROUP 2818

U.S. PATENT DOCUMENTS						
EXAM- INER INI- TIAL	REF. NO.	DOCUMENT NUMBER Number-Kind Code (if known)	ISSUE DATE / PUBLICATION DATE MM-DD-YYYY	NAME OF PATENTEE OR APPLICANT OF CITED DOCUMENT		
	AG10	6,001,669	12-14-1999	Gaines, et al.		
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SUPPLEMENTAL INFORMATION DISCLOSURE CITATION IN AN APPLICATION	FIRST NAMED INVENTOR Jagdish Narayan			FILING DATE June 27, 2003	
November 4, 2004 (Use several sheets if necessary)	EXAMINER Nhu, David	CONF 8117	IRMATION NO.	GROUP 2818	

	F	OREIGN PATENT D	OCUMENTS	
	DOCUMENT NUMBER Country Code-Number-Kind Code (if known)	DATE MM-DD-YYYY	NAME OF PATENTEE OR APPLICANT OF CITED DOCUMENT	TRANSLATION YES NO
AP6	EP 0 513 745 A2	11-19-1992	CSELT Centro Studi e Laboratori Telecomunicazioni S.p.A.	
AQ6	WO 01/73858 A1	10-04-2001	Toyoda Gosei Co., Ltd.	X
AL7	WO 01/47038 A1	06-28-2001	Lumileds Lighting	
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AP7	DE 100 60 439 A	06-13-2002	OSRAM Opto Semiconductors GmbH & Co.	X
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EXAMINER	DATE CONSIDERED
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Sheet 4 of 4

PTO-1449 REPRODUCED			pplication no. 0/608,780	
SUPPLEMENTAL INFORMATION DISCLOSURE CITATION IN AN APPLICATION	FIRST NAMED INVENTOR Jagdish Narayan		FILING DATE June 27, 2003	
November 4, 2004 (Use several sheets if necessary)	EXAMINER Nhu, David	CONFI 8117	RMATION NO.	GROUP 2818

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AV6	Chichibu, S., et al., "Exciton Localization in InGaN Quantum Well Devices," J. Vac. Sci. Technol B., Vol. 16(4):2204-2214 (1998).
AW6	Chen, L., et al., "Fabrication of 50-100 nm Patterned InGaN Blue Light Emitting Heterostructures," IEEE, 14th Annual Meeting of the IEEE Lasers & Electro-Optics Society, 1:760-761 (2001).
AX6	Cho, H. K., et al., "Influence of Strain-Induced Indium Clustering on Characteristics of InGaN/GaN Multiple Quantum Wells with High Indium Composition," <i>Journal of Applied Physics</i> , 91(3):1104-1107 (2002).
AY6	Narayan, J. and H. Wang, "Effect of Thickness Variation in High-Efficiency InGaN/GaN Light-Emitting Diodes," <i>Applied Physics Letters</i> , 81(5): 841-843 (2002).
AZ6	Kim, H., et al., "Design and Fabrication of Highly Efficient GaN-Based Light-Emitting Diodes," <i>IEEE Transactions on Electron Devices</i> , 49(10):1715-1722 (2002).
AR7	Maeda, T., et al., "Effects of NiO on Electrical Properties of NiAu-Based Ohmic Contacts for p-type GaN," Applied Physics Letters 75(26):4145-4147 (1999).
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